

# **Thyristor Module**

= 2x 1600 V

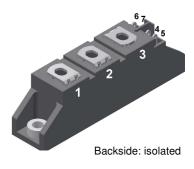
27 A

 $V_{\tau}$ 1.27 V

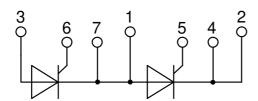
## Phase leg

#### Part number

#### MCC26-16io1B







#### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

#### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

#### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

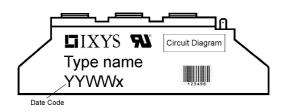
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Thyristo				<b>"</b>	Ratings	<b>&gt;</b>	1
Symbol	Definition	Conditions		min.	typ.	max.	Ur
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward bl	ocking voltage	$T_{VJ} = 25^{\circ}C$			1600	
R/D	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 125$ °C			3	m
V <sub>T</sub>	forward voltage drop	I <sub>T</sub> = 40 A	$T_{VJ} = 25^{\circ}C$			1.27	
		$I_T = 80 \text{ A}$				1.64	
		$I_T = 40 \text{ A}$	T <sub>vJ</sub> = 125°C			1.27	
		$I_{T} = 80 \text{ A}$				1.65	
I <sub>TAV</sub>	average forward current	$T_c = 85^{\circ}C$	T <sub>vJ</sub> = 125°C			27	
T(RMS)	RMS forward current	180° sine				42	
V <sub>T0</sub>	threshold voltage		T <sub>v.i</sub> = 125°C			0.85	
r <sub>T</sub>	slope resistance } for power lo	oss calculation only	VJ			11	m
R <sub>thJC</sub>	thermal resistance junction to cas	e				0.88	!
R <sub>thCH</sub>	thermal resistance case to heatsin				0.20	*****	K/V
P <sub>tot</sub>	total power dissipation	***	T <sub>c</sub> = 25°C		0.20	115	٧
l <sub>TSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VI} = 45^{\circ}C$			520	
TSM	max. Torward darge darrent	t = 8,3  ms; (60  Hz),  sine	$V_R = 0 V$			560	
		t = 0.5  ms, (60 Hz), sine t = 10  ms; (50 Hz), sine	$V_R = 0 V$ $T_{VJ} = 125 ^{\circ}C$			440	
						_	į
lo.	value for fueing	t = 8,3 ms; (60 Hz), sine	V <sub>R</sub> = 0 V			475	1- 4.3
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.35	kA <sup>2</sup>
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.31	1
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 125$ °C			970	A <sup>2</sup>
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			940	A <sup>2</sup>
C,	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		22		р
$P_{GM}$	max. gate power dissipation	t <sub>P</sub> = 30 μs	$T_{C} = 125^{\circ}C$			10	٧
		t <sub>P</sub> = 300 μs				5	٧
$P_{GAV}$	average gate power dissipation					0.5	٧
(di/dt) <sub>cr</sub>	critical rate of rise of current	$T_{VJ} = 125 ^{\circ}\text{C}; f = 50 \text{ Hz}$ rep	petitive, $I_T = 45 A$			150	A/μ
		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu s;$					
		$I_{G} = 0.45 A; V = \frac{2}{3} V_{DRM}$ no	n-repet., $I_T = 27 A$			500	$A/\mu$
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	T <sub>vJ</sub> = 125°C			1000	V/μ
		R <sub>GK</sub> = ∞; method 1 (linear voltag	ge rise)				
V <sub>GT</sub>	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	١
			$T_{VJ} = -40$ °C			1.6	١
I <sub>GT</sub>	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			100	m
<b>u</b> .		, and the second	$T_{VJ} = -40$ °C			200	m
V <sub>GD</sub>	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DBM}$	$T_{VJ} = 125^{\circ}C$			0.2	,
I <sub>GD</sub>	gate non-trigger current	- U / C - DRW	. 43			10	m
-gb   <sub>L</sub>	latching current	t <sub>p</sub> = 10 μs	T <sub>VJ</sub> = 25°C			450	m
IL.	latoring carrent	$I_g = 0.45 \text{ A}; \text{ di}_g/\text{dt} = 0.45 \text{ A}/\mu\text{s}$				430	1117
1	holding current		T <sub>vJ</sub> = 25°C			200	m
l <sub>н</sub>		$V_D = 6 V R_{GK} = \infty$					<u> </u>
t <sub>gd</sub>	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$			2	μ
_	$I_{G} = 0.45 \text{ A}; \text{ di}_{G}/\text{dt} = 0.45 \text{ A}/\mu\text{s}$						
t <sub>q</sub>	turn-off time	$V_R = 100 \text{ V}; I_T = 20 \text{ A}; V = \frac{2}{3}$			150		μ
		$di/dt = 10 A/\mu s dv/dt = 20 V/$	μs t <sub>p</sub> = 200 μs				1 1 1



Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
RMS	RMS current	per terminal					200	Α
T <sub>VJ</sub>	virtual junction temperature				-40		125	°C
Top	operation temperature				-40		100	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						81		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d <sub>Spp/App</sub>	creepage distance on surface	striking distance through air	terminal to terminal 13.0 terminal to backside 16.0		9.7			mm
$d_{Spb/Apb}$	creepage distance on surface (	striking distance through an			16.0			mm
V <sub>ISOL</sub>	isolation voltage	isolation voltage t = 1 second			3600			٧
.002	t = 1 minute		50/60 Hz, RMS; lisoL ≤ 1 mA		3000			٧



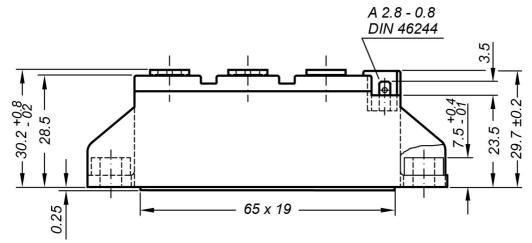
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC26-16io1B	MCC26-16io1B	Box	36	452866

Similar Part	Package	Voltage class	
MCMA35P1600TA	TO-240AA-1B	1600	
MCMA50P1600TA	TO-240AA-1B	1600	

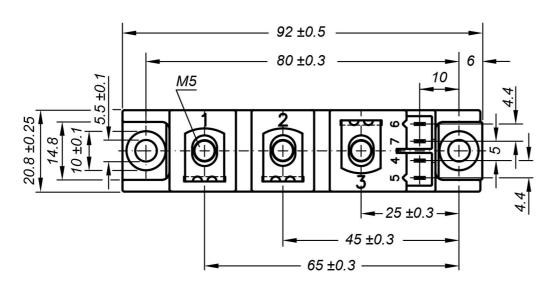
Equiva	alent Circuits for	Simulation	* on die level	T <sub>vJ</sub> = 125 °C
$I \rightarrow V_0$	)—[R <sub>0</sub> ]-	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.85		V
$R_{0 \text{ max}}$	slope resistance *	9.8		mΩ



### **Outlines TO-240AA**

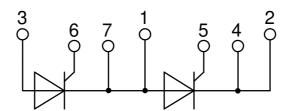


General tolerance: DIN ISO 2768 class "c"



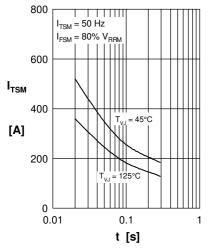
Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751

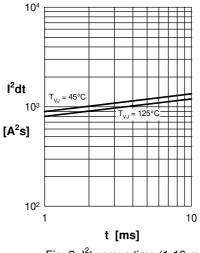
Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)





### **Thyristor**





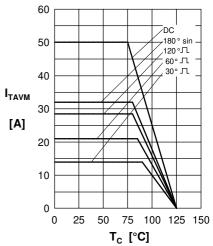
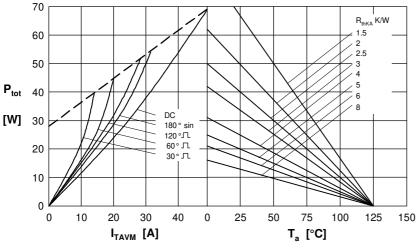


Fig. 1 Surge overload current  $I_{TSM}$ ,  $I_{FSM}$ : Crest value, t: duration

Fig. 2 I<sup>2</sup>t versus time (1-10 ms)

Fig. 3 Max. forward current at case temperature



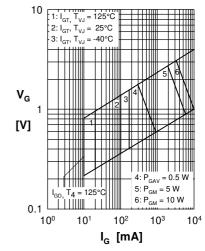
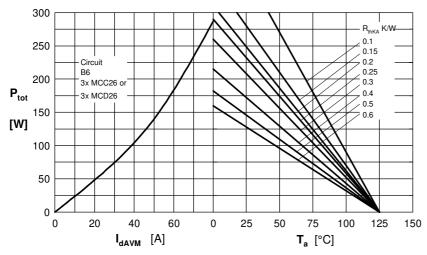


Fig. 4 Power dissipation vs. on-state current & ambient temperature (per thyristor or diode)

Fig. 5 Gate trigger characteristics



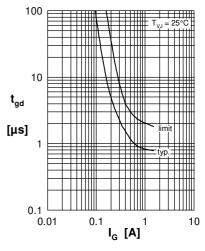


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

Fig. 7 Gate trigger delay time



### **Thyristor**

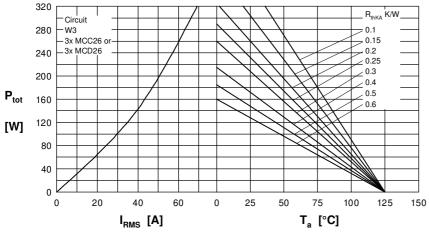


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

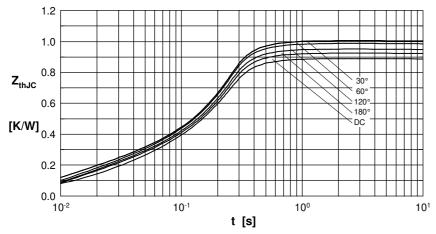


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

 $R_{thJC}$  for various conduction angles d:

d	R <sub>thJC</sub> [K/W]
DC	0.88
180°	0.92
120°	0.95
60°	0.98
30°	1.01

Constants for  $\mathbf{Z}_{\text{thJC}}$  calculation:

i	$R_{thi}$ [K/W]	t <sub>i</sub> [s]
1	0.019	0.0031
2	0.029	0.0216
2	0 833	0.1010

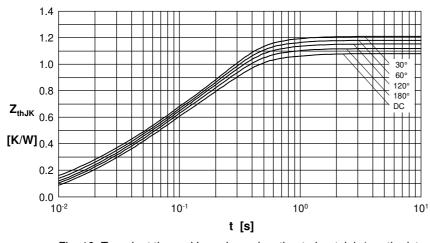


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

 $\mathbf{R}_{\text{thJK}}$  for various conduction angles d:

d	$R_{thJK}$ [K/W]
DC	1.08
180°	1.12
120°	1.15
60°	1.18
30°	1.21

Constants for  $Z_{\text{thJK}}$  calculation:

i	$R_{thi}$ [K/W]	t <sub>i</sub> [s]
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.1910
4	0.200	0.4500

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Data according to IEC 60747and per semiconductor unless otherwise specified

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